



(12) **Patent Application Publication**
SHIN et al.

(10) **Pub. No.: US 2018/0252956 A1**
(43) **Pub. Date: Sep. 6, 2018**

- CPC **G02F 1/13338** (2013.01); **G02F 2001/134372** (2013.01); **G02F 1/134309** (2013.01); **G02F 1/13439** (2013.01); **G06F 3/0412** (2013.01); **G02F 1/136286** (2013.01); **G06F 3/047** (2013.01); **G02F 1/133345** (2013.01); **G06F 3/044** (2013.01); **G02F 1/1368** (2013.01); **G06F 3/041** (2013.01); **G02F 2001/133302** (2013.01); **G02F 2001/136295** (2013.01); **G06F 2203/04103** (2013.01); **G02F 1/133514** (2013.01)

- (22) Filed: **May 3, 2018**

(63) Continuation of application No. 15/156,243, filed on May 16, 2016, now Pat. No. 9,977,274, which is a continuation of application No. 13/722,366, filed on Dec. 20, 2012, now Pat. No. 9,759,940.

Dec. 22, 2011 (KR) 10-2011-0140094

(51) Int. Cl.

G02F 1/1333 (2006.01)
G02F 1/1335 (2006.01)
G02F 1/1343 (2006.01)
G06F 3/041 (2006.01)

(57) **ABSTRACT**

Disclosed is an LCD device which realizes decreased thickness, simplified process, and decreased cost by using a common electrode for formation of electric field to drive liquid crystal as a sensing electrode, and removing a touch screen from an upper surface of the liquid crystal panel, the LCD device comprising gate and data lines crossing each other to define plural pixels on a lower substrate; a pixel electrode in each of the plural pixels; plural common electrode blocks patterned at the different layer from the pixel electrode, wherein the common electrode blocks, together with the pixel electrode, forms an electric field, and senses a user's touch; and plural sensing lines electrically connected with the common electrode blocks, wherein, if the sensing line is electrically connected with one of the common electrode blocks, the sensing line is insulated from the remaining common electrode blocks.

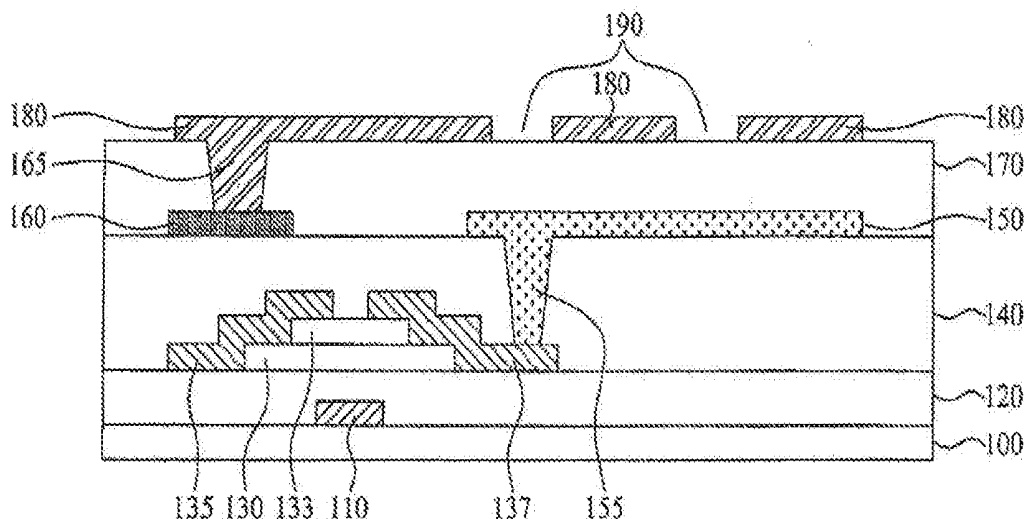


FIG. 1
[Related Art]

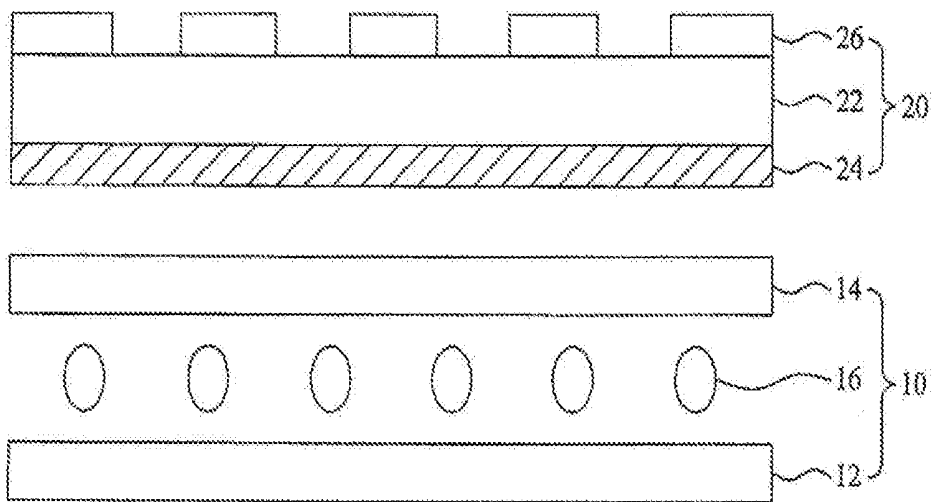


FIG. 2A

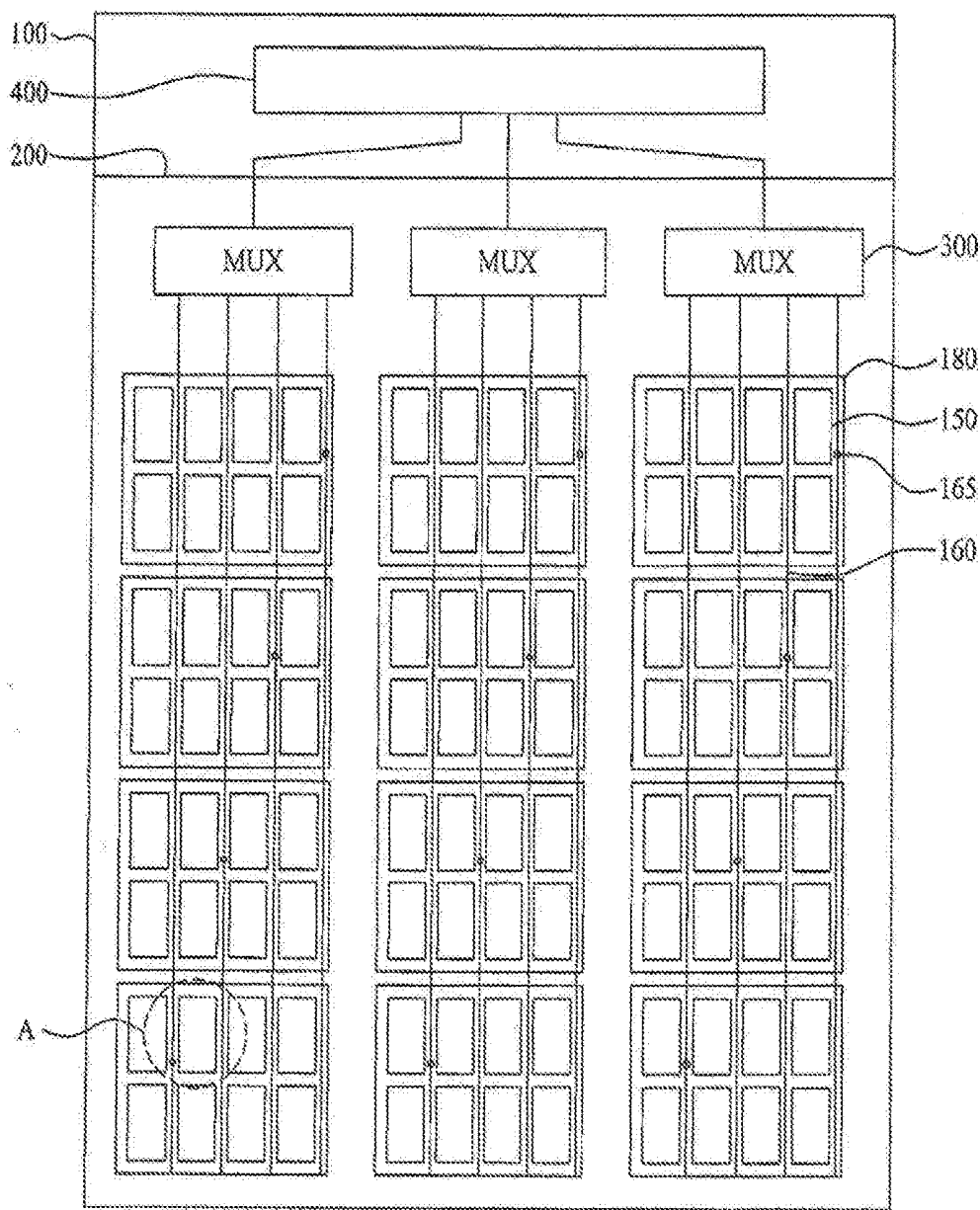


FIG. 2B

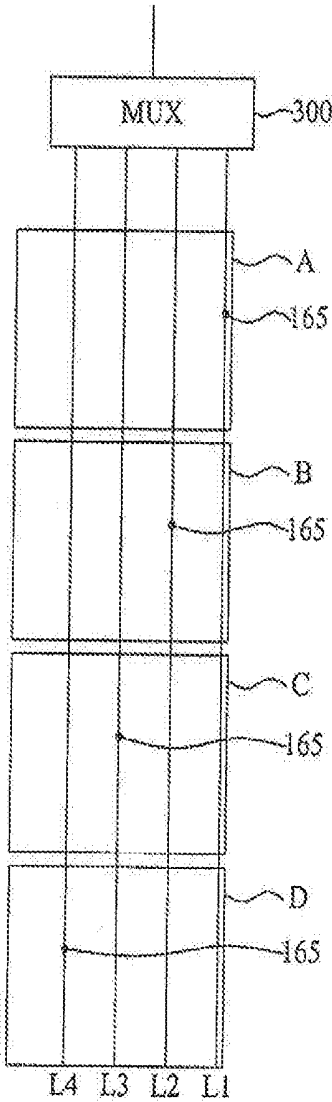


FIG. 3

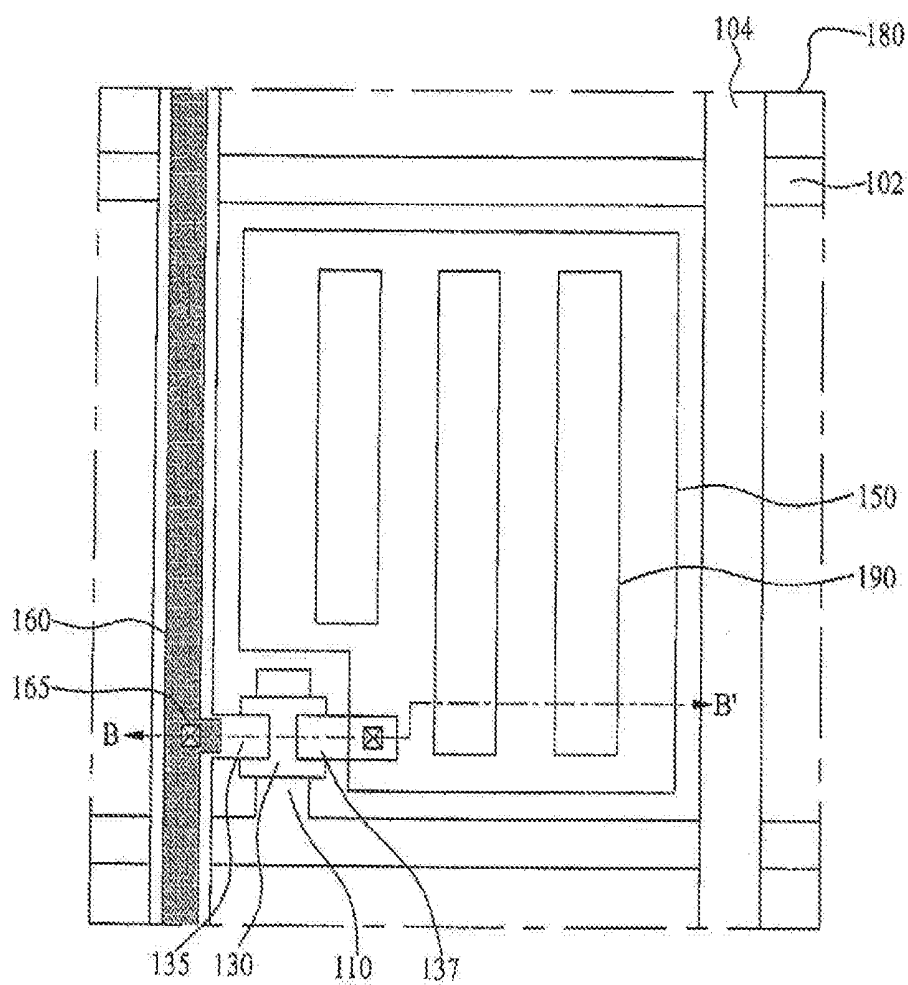


FIG. 4

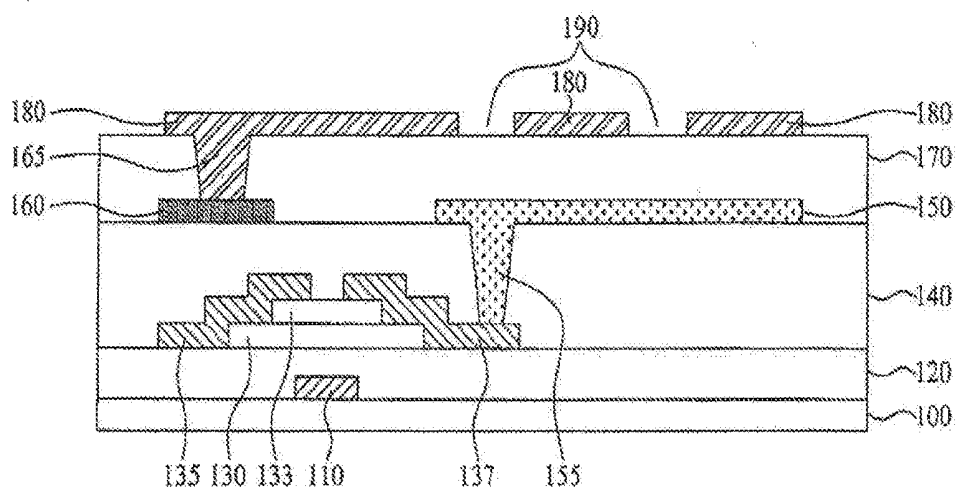


FIG. 5

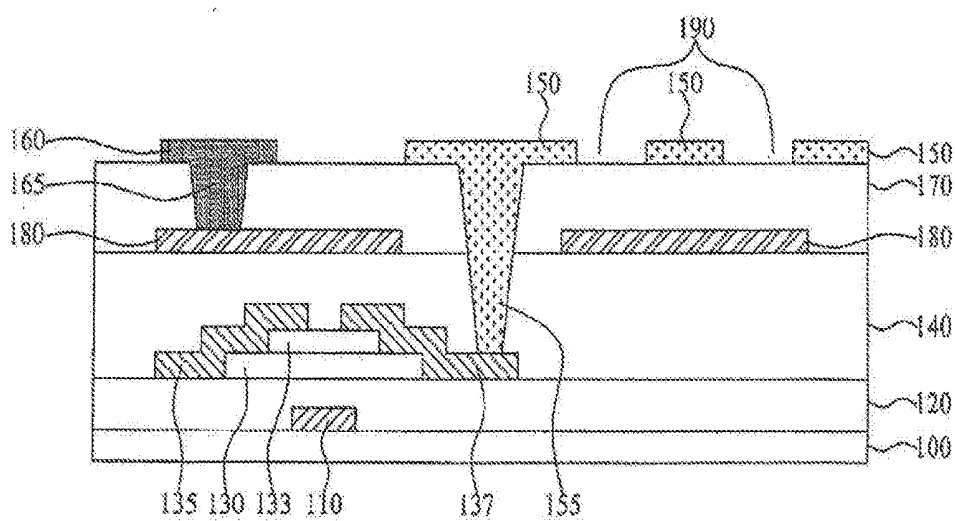


FIG. 6

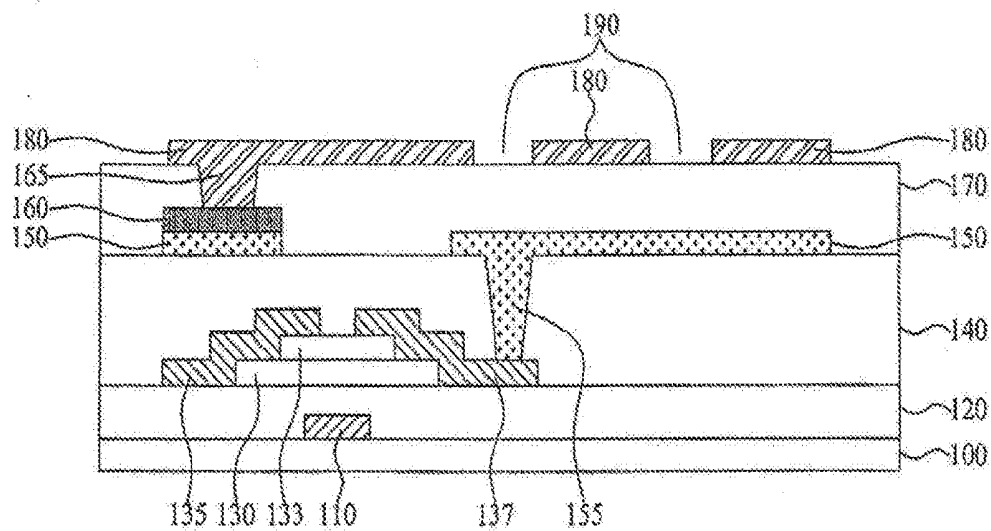


FIG. 7

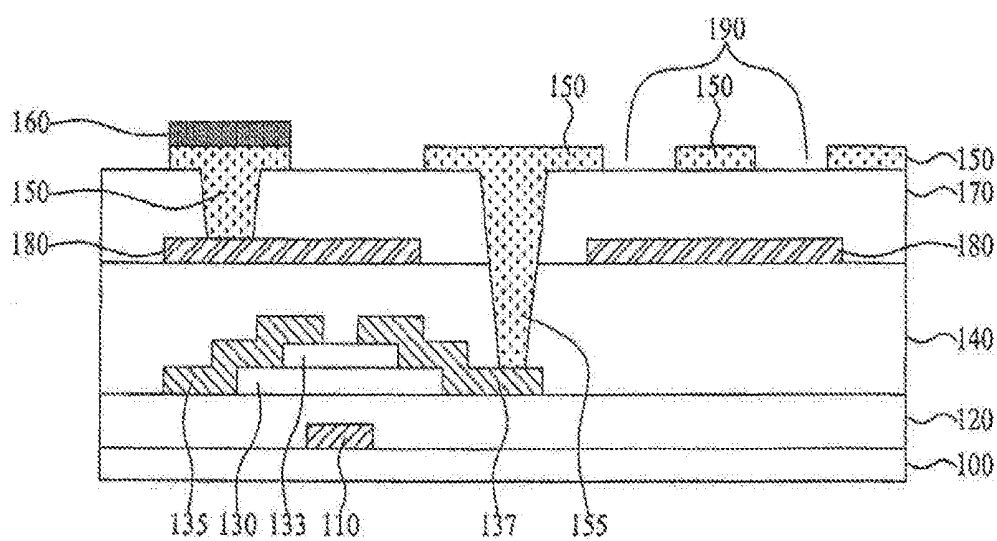


FIG. 8

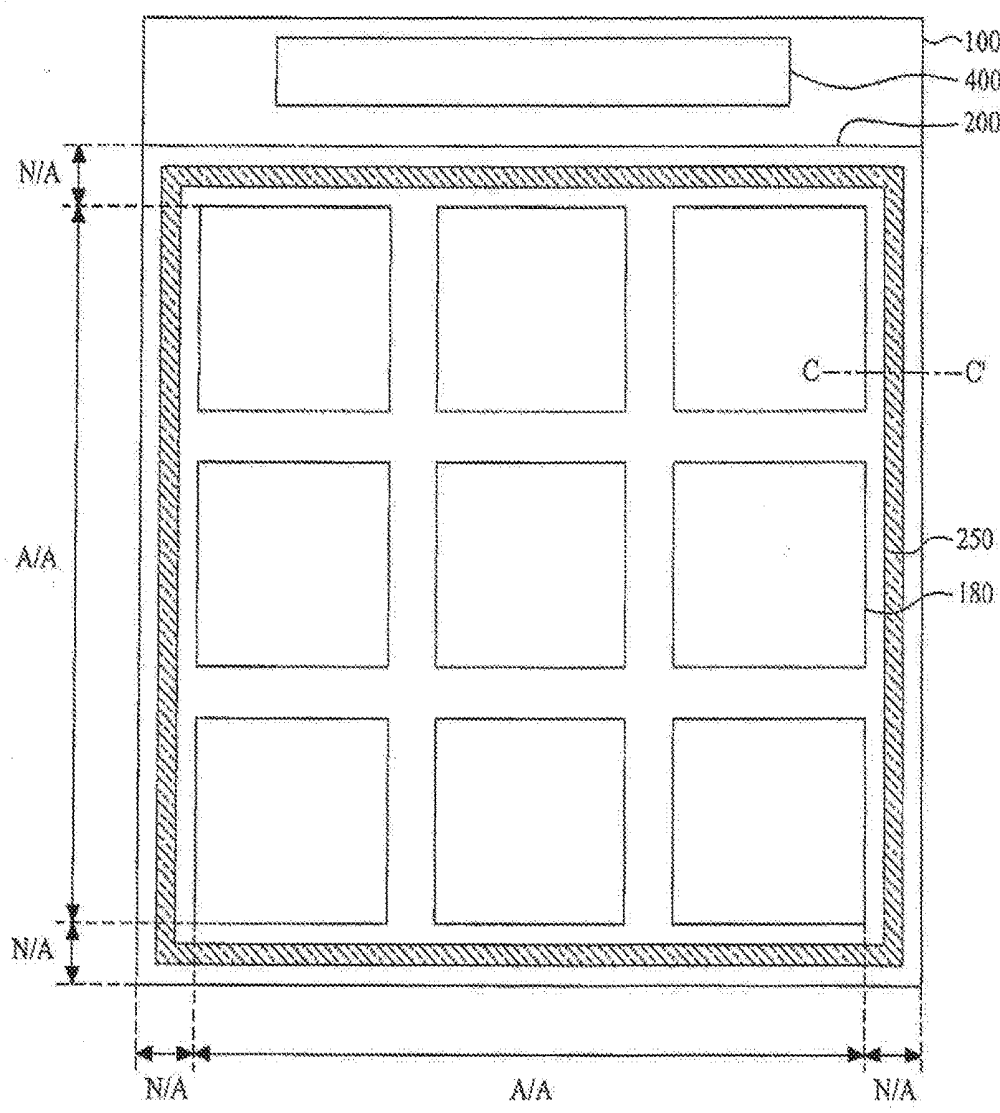


FIG. 9

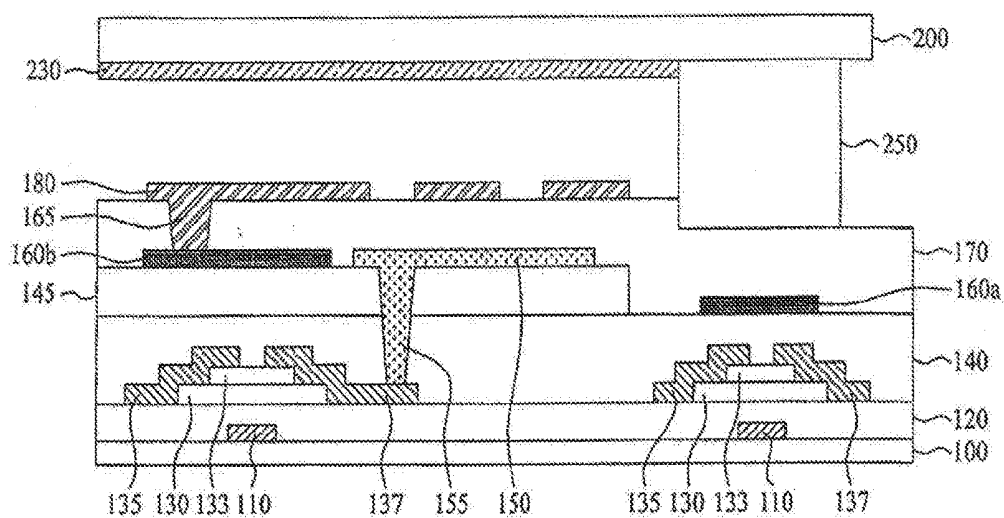


FIG. 10

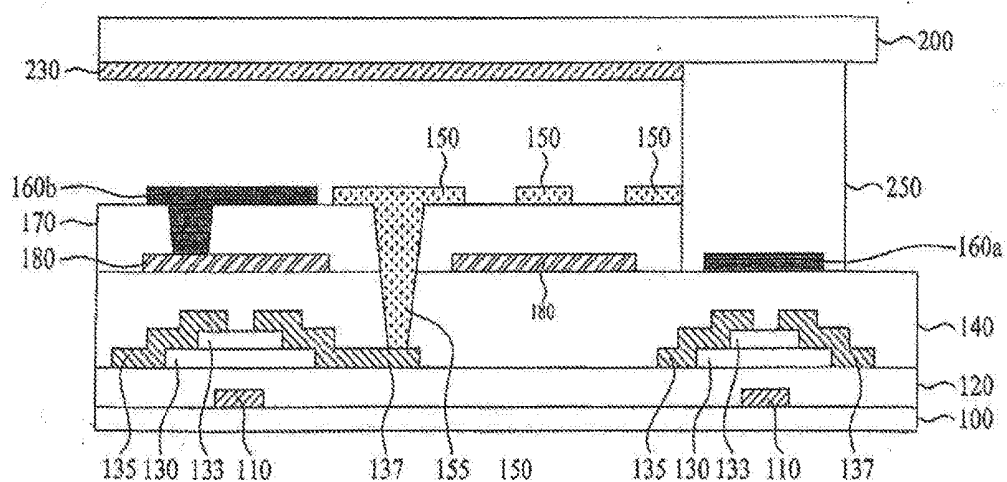


FIG. 11A

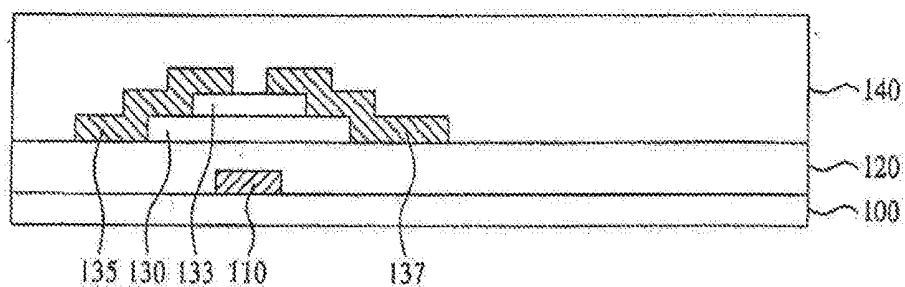


FIG. 11B

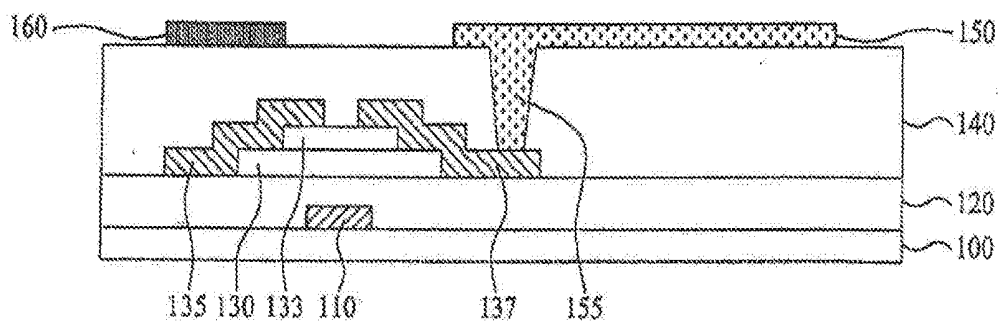


FIG. 11C

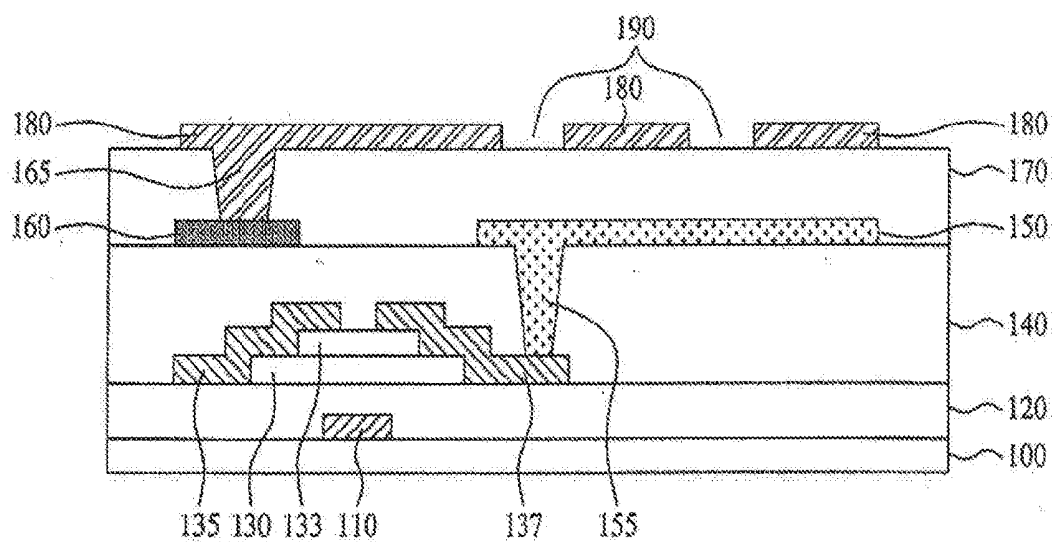


FIG. 12A

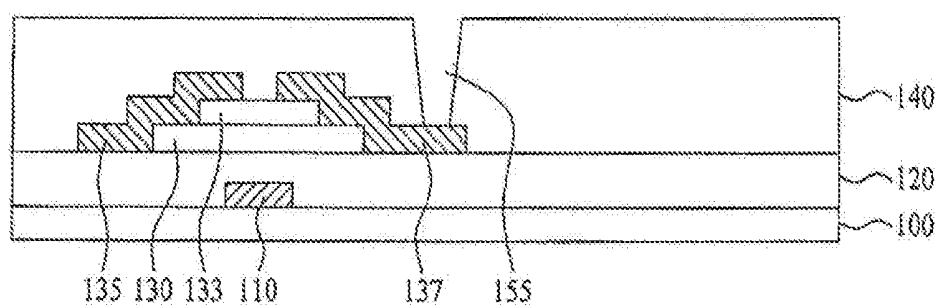


FIG. 12B

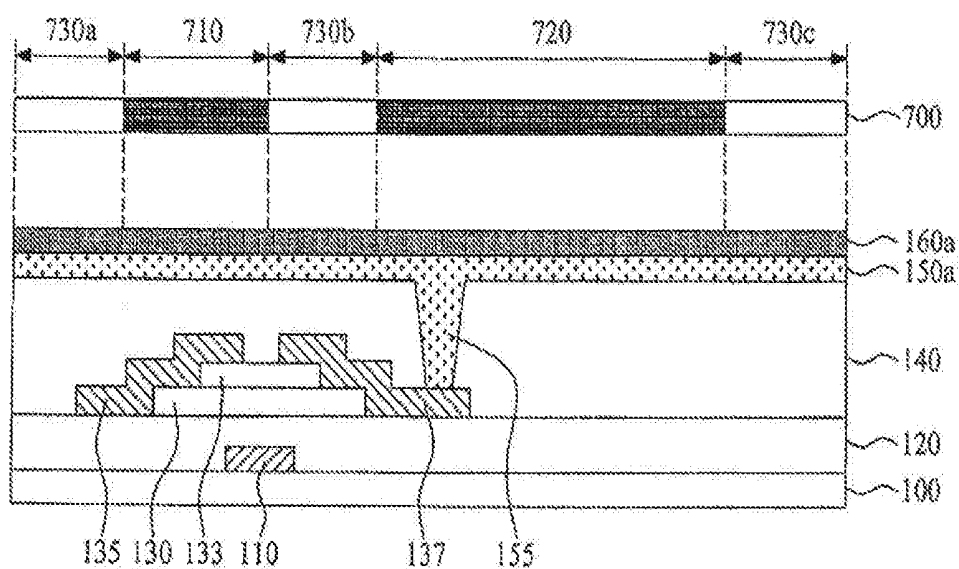


FIG. 12C

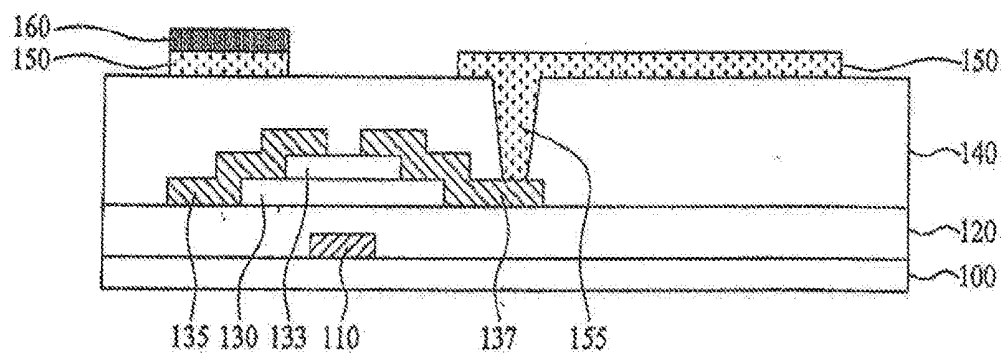


FIG. 12D

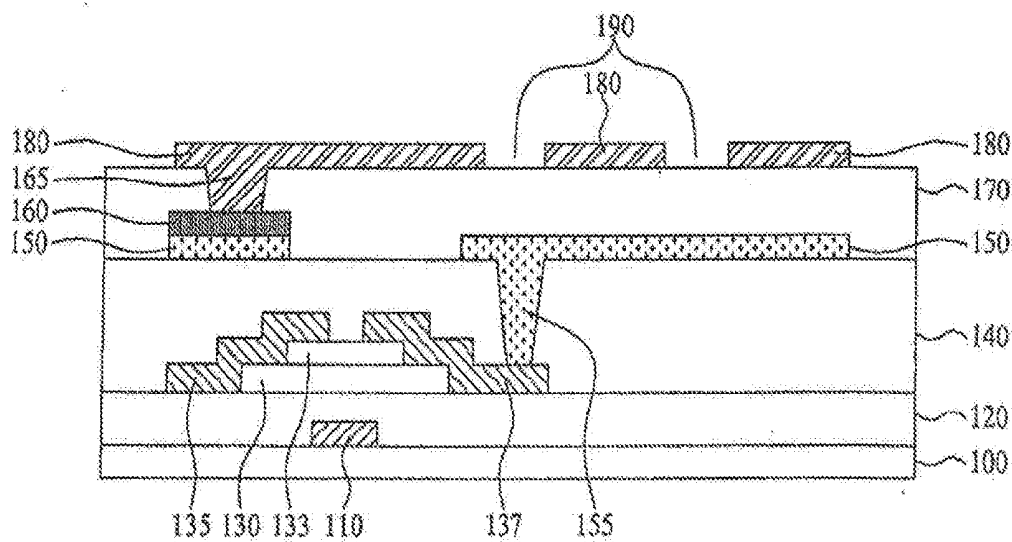


FIG. 13A

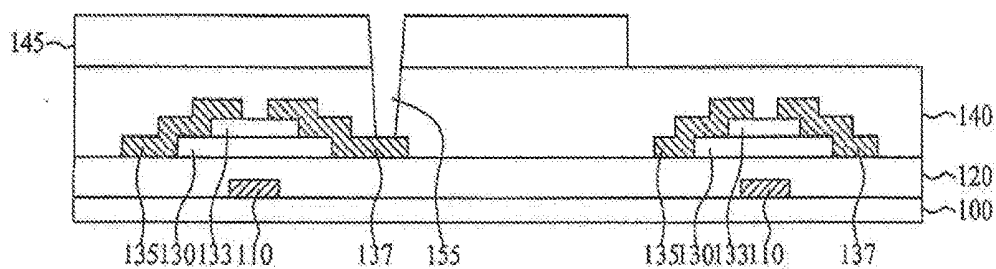


FIG. 13B

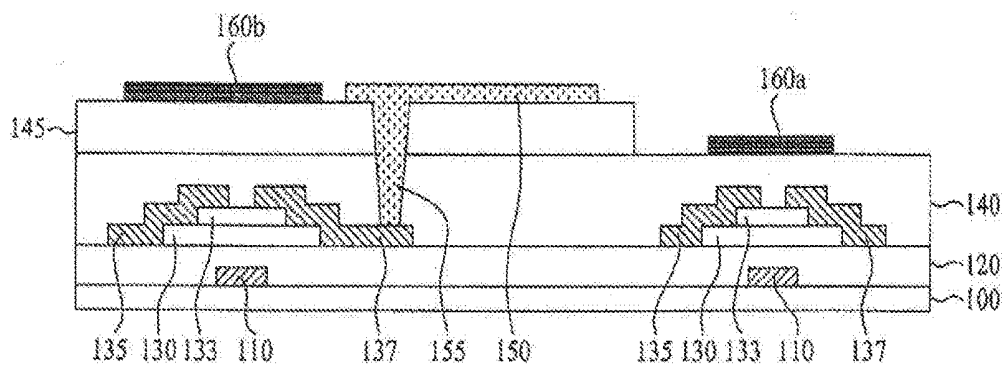


FIG. 13C

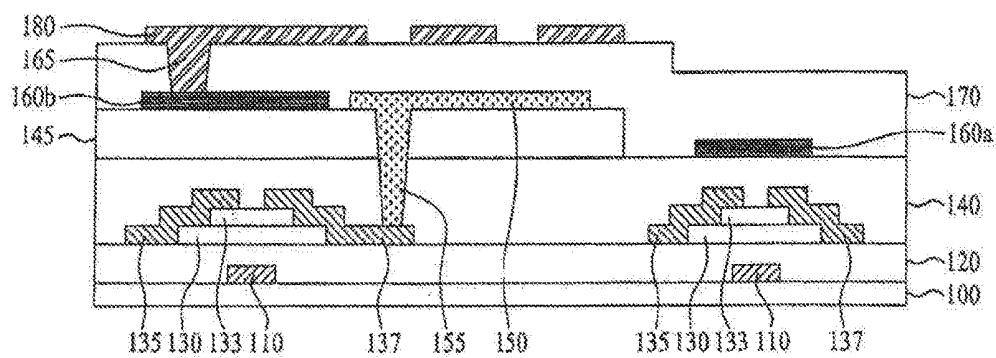


FIG. 13D

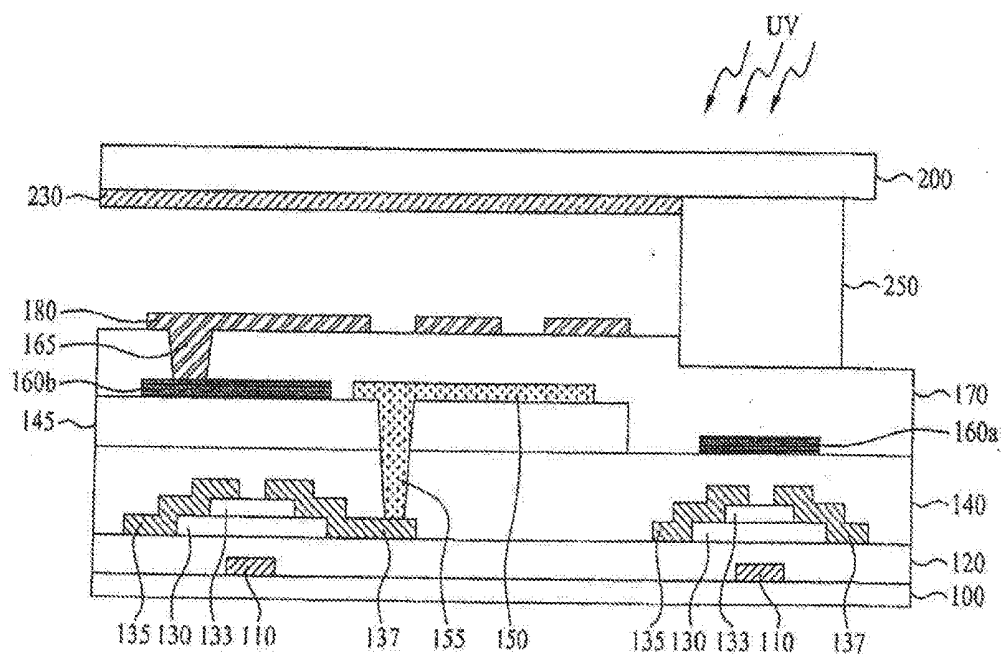
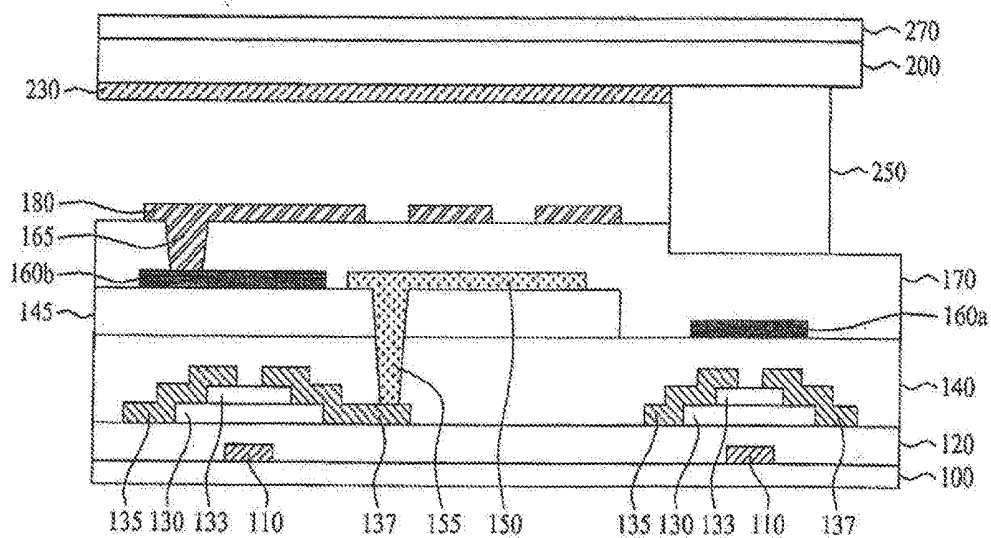


FIG. 14



DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME

CROSS REFERENCE TO RELATED APPLICATIONS

[0001] This application claims the benefit of the Korean Patent Application No. 10-2011-0140094 filed on Dec. 22, 2011, which is hereby incorporated by reference as if fully set forth herein.

BACKGROUND

Field of the Disclosure

[0002] The present disclosure relates to a liquid crystal display (LCD) device, and more particularly, to a liquid crystal display (LCD) device with a sensing electrode for sensing a user's touch.

Discussion of the Related Art

[0003] Owing to advantages such as good portability and low power consumption by low operating voltage, a liquid crystal display (LCD) device is widely used in various fields of notebook computer, monitor, spacecraft, aircraft, etc.

[0004] The LCD device includes a lower substrate, an upper substrate, and a liquid crystal layer formed between the lower and upper substrates. According to whether or not an electric field is applied, light transmittance is controlled by alignment of the liquid crystal layer, to thereby display images.

[0005] Generally, the LCD device is provided with input means such as mouse or keyboard. However, in case of navigation, portable terminal and home appliances, a touch screen is typically used, which enables to directly input information to a screen through the use of finger or pen.

[0006] A related art LCD device with a touch screen applied thereto will be described below.

[0007] FIG. 1 is a cross sectional view of an LCD device according to the related art. As shown in FIG. 1, the LCD device according to the related art includes a liquid crystal panel 10 and a touch screen 20.

[0008] The liquid crystal panel 10 is provided to display images thereon, wherein the liquid crystal panel 10 includes a lower substrate 12, an upper substrate 14, and a liquid crystal layer 16 between the lower and upper substrates 12 and 14.

[0009] The touch screen 20 is formed on an upper surface of the liquid crystal panel 10, to thereby sense a user's touch. The touch screen 20 includes a touch substrate 22, a first sensing electrode 24 on a lower surface of the touch substrate 22, and a second sensing electrode 26 on an upper surface of the touch substrate 22.

[0010] The first sensing electrode 24 is arranged in a horizontal direction on the lower surface of the touch substrate 22, and the second sensing electrode 26 is formed in a vertical direction on the upper surface of the touch substrate 22. If a user touches a predetermined position, a capacitance between the first sensing electrode 24 and the second sensing electrode 26 is changed at the touched position. Thus, it is possible to sense the user's touch by sensing the touched position with the changed capacitance.

[0011] However, since the LCD device according to the related art is formed in a structure with the touch screen 20 additionally provided on the upper surface of the liquid

crystal panel 10, it may cause disadvantages such as a decreased total thickness of the device, a complicated manufacturing process and an increased manufacturing cost.

SUMMARY

[0012] An LCD device comprises: gate and data lines crossing each other to define plural pixels on a lower substrate; a pixel electrode in each of the plural pixels; plural common electrode blocks patterned at the different layer from the pixel electrode, wherein the common electrode blocks, together with the pixel electrode, forms an electric field, and senses a user's touch; and plural sensing lines electrically connected with the common electrode blocks, wherein, if the sensing line is electrically connected with one of the common electrode blocks, the sensing line is insulated from the remaining common electrode blocks.

[0013] In another aspect, there is provided an LCD Device comprising: an active area of a lower substrate including gate and data lines crossing each other to define a plurality of pixels; a transistor in each of the pixels; a pixel electrode in each of the pixels; plural common electrode blocks formed at the different layer from the pixel electrode, wherein the common electrode blocks, together with the pixel electrode, forms an electric field, and senses a user's touch; and plural sensing lines electrically connected with the common electrode blocks; a dummy area along the edge of the active area; and a blocking layer on a semiconductor layer of the transistor formed in the active area and the dummy area, the blocking layer for blocking ultraviolet rays, wherein, if the sensing line is electrically connected with one of the common electrode blocks, the sensing line is insulated from the remaining common electrode blocks.

[0014] In another aspect, there is provided a method for manufacturing an LCD device comprising: sequentially forming a gate electrode, a gate insulating film, a semiconductor layer, a source electrode, a drain electrode, and a first passivation layer on a lower substrate; forming a pixel electrode after forming a pixel electrode contact hole in the first passivation layer, and electrically connecting the pixel electrode and the drain electrode with each other through the pixel electrode contact hole; forming plural sensing lines in a predetermined direction, wherein the sensing line is formed on the first passivation layer, and is provided at a predetermined interval from the pixel electrode; forming a second passivation layer on the pixel electrode and the sensing line, and forming a common electrode contact hole so as to make the sensing line connected with one of plural common electrode blocks, and simultaneously make the sensing line insulated from the remaining common electrode blocks; and forming the common electrode block on the second passivation layer so as to electrically connect the sensing line and the common electrode block with each other.

[0015] It is to be understood that both the foregoing general description and the following detailed description of the present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0016] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this application,

illustrate embodiment(s) of the invention and together with the description serve to explain the principle of the invention. In the drawings:

[0017] FIG. 1 is a cross sectional view of an LCD device according to the related art;

[0018] FIG. 2A is a plane view of a lower substrate for an LCD device according to one embodiment of the present invention, and FIG. 2B shows a principle of sensing a user's touch position in a sensing line according to an embodiment of the present invention;

[0019] FIG. 3 is an expanded view showing 'A' of FIG. 2A;

[0020] FIG. 4 is a cross sectional view showing one embodiment along B-B' of FIG. 3;

[0021] FIG. 5 is a cross sectional view showing another embodiment along B-B' of FIG. 3;

[0022] FIG. 6 is a cross sectional view showing another embodiment along B-B' of FIG. 3;

[0023] FIG. 7 is a cross sectional view showing another embodiment along B-B' of FIG. 3;

[0024] FIG. 8 illustrates an LCD device according to another embodiment of the present invention;

[0025] FIG. 9 is a cross sectional view showing one embodiment along C-C' of FIG. 8;

[0026] FIG. 10 is a cross sectional view showing another embodiment along C-C' of FIG. 8;

[0027] FIGS. 11A to 11C are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to one embodiment of the present invention;

[0028] FIGS. 12A to 12D are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to another embodiment of the present invention;

[0029] FIGS. 13A to 13D are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to another embodiment of the present invention; and

[0030] FIG. 14 is a cross sectional view showing another embodiment along C-C' of FIG. 8.

DETAILED DESCRIPTION OF THE EXEMPLARY EMBODIMENTS

[0031] Reference will now be made in detail to the exemplary embodiments of the present invention, examples of which are illustrated in the accompanying drawings. Wherever possible, the same reference numbers will be used throughout the drawings to refer to the same or like parts.

[0032] Hereinafter, a liquid crystal display (LCD) device according to the present invention and a method for manufacturing the same will be described with reference to the accompanying drawings.

[0033] On explanation about the embodiments of the present invention, if it is mentioned that a first structure is positioned 'on or above' or 'under or below' a second structure, it should be understood that the first and second structures are brought into contact with each other, or a third structure is interposed between the first and second structures.

Liquid Crystal Display (LCD) Device

[0034] FIG. 2A is a plane view of a lower substrate for an LCD device according to one embodiment of the present invention, FIG. 2B shows a principle of sensing a user's

touch position in a sensing line according to the present invention, and FIG. 3 is an expanded view showing 'A' of FIG. 2A.

[0035] As shown in FIGS. 2A and 3, the LCD device according to the present invention includes a lower substrate 100, a gate line 102, a data line 104, a gate electrode 110, a semiconductor layer 130, a source electrode 135, a drain electrode 137, a pixel electrode 150, a sensing line 160, a common electrode contact hole 165, a common electrode block 180, a slit 190, an upper substrate 200, a multiplexer 300, and a sensing circuit 400.

[0036] The lower substrate 100 may be formed of glass or transparent plastic.

[0037] The gate line 102 is arranged along a horizontal direction on the lower substrate 100, and the data line 104 is arranged along a vertical direction on the lower substrate 100. The gate line 102 and the data line 104 cross each other, to thereby define a plurality of pixels.

[0038] Both the gate line 102 and the data line 104 are formed in straight-line shapes, but not necessarily. For example, the data line 104 may be formed in a curved-line shape.

[0039] A thin film transistor, which functions as a switching element, is formed in each of the pixels. The thin film transistor includes the gate electrode 110, the semiconductor layer 130, the source electrode 135, and the drain electrode 137. The thin film transistor may be formed in a bottom gate structure where the gate electrode 110 is positioned below the semiconductor layer 130, or may be formed in a top gate structure where the gate electrode 110 is positioned above the semiconductor layer 130.

[0040] The pixel electrode 150 is formed in each of the pixels. Especially, the pixel electrode 150 is formed in a shape corresponding to that of the pixel.

[0041] The common electrode block 180 and the pixel electrode 150 are formed at different layers. Thus, the common electrode 180, together with the pixel electrode 150, forms an electric field so as to drive liquid crystal and simultaneously functions as a sensing electrode for sensing a user's touch position.

[0042] In order to use the common electrode block 180 as the sensing electrode, the plurality of common electrode blocks 180 are patterned. The plurality of common electrode blocks 180 may be formed in a size corresponding to a size of one or more pixels. Herein, the size of common electrode blocks 180 deeply affects touch resolution of the LCD device. That is, the touch resolution of the LCD device is highly affected by the number of pixels to be corresponding to the size of common electrode blocks 180.

[0043] If an area corresponding to a large number of pixels is provided for one common electrode block 180, the touch resolution is lowered to that extent. Meanwhile, an area corresponding to a small number of pixels is provided for one common electrode block 180, the touch resolution is improved, however, the number of sensing lines 160 is increased.

[0044] The sensing line 160 applies an electrical signal to the plural common electrode blocks 180. That is, the plural common electrode blocks 180 are connected with the sensing line 160. At an end of the sensing line 160, there is the sensing circuit 400 for sensing the user's touch position.

[0045] If the sensing line 160 is electrically connected with one of the common electrode blocks 180, the sensing

line 160 is insulated from the remaining common electrode blocks 180, to thereby sense the user's touch position.

[0046] For a detailed explanation, FIG. 2B illustrates the four common electrode blocks (A, B, C, D) 180 and the four sensing lines 160.

[0047] As shown in FIG. 2B, the sensing line (L1) 160 is connected with the common electrode block (A) 180, and is insulated from the other common electrode blocks (B, C, D) 180. Thus, if the user touches the common electrode block (A) 180, this signal is transmitted to the sensing line (L1) 160, to thereby sense the user's touch position.

[0048] In the same manner, the sensing line (L2) 160 is connected with the common electrode block (B) 180, and is insulated from the other common electrode blocks (A, C, D) 180. Thus, if the user touches the common electrode block (B) 180, this signal is transmitted to the sensing line (L2) 160, to thereby sense the user's touch position.

[0049] The sensing line (L3) 160 is connected with the common electrode block (C) 180, and is insulated from the other common electrode blocks (A, B, D) 180. Thus, if the user touches the common electrode block (C) 180, this signal is transmitted to the sensing line (L3) 160, to thereby sense the user's touch position.

[0050] The sensing line (L4) 160 is connected with the common electrode block (D) 180, and is insulated from the other common electrode blocks (A, B, C) 180. Thus, if the user touches the common electrode block (D) 180, this signal is transmitted to the sensing line (L4) 160, to thereby sense the user's touch position.

[0051] As described above, if using the structure of the common electrode block 180 and the sensing line 160, it is possible to sense the user's touch position on the X-Y coordinates plane through the use of sensing line 160 extending in one direction of the lower substrate 100.

[0052] In comparison with the LCD device with the sensing line 160 formed both in the X-axis direction and the Y-axis direction, the LCD device according to the present invention enables to simplify the structure and to reduce cost.

[0053] Referring again to FIG. 3, the sensing line 160 applies the electrical signal to the common electrode block 180, and simultaneously reduces resistance of the common electrode block 180.

[0054] Generally, the common electrode block 180 is formed of a transparent conductive material such as Indium-Tin-Oxide (ITO), wherein the transparent conductive material has high resistance. According as the common electrode block 180 is connected with the sensing line 160 which is formed of a metal material with high conductivity, it is possible to reduce the resistance of the common electrode block 180. For example, the sensing line 160 may be formed of any one selected among molybdenum (Mo), aluminum (Al) and copper (Cu), or their alloys.

[0055] The sensing line 160 may be formed in a direction parallel to the gate line 102 or the data line 104. According to the present invention, even though the sensing line 160 is formed in a direction parallel to the gate line 102 or the data line 104, it is possible to sense the user's touch position on the X-Y coordinates plane.

[0056] In order to prevent an aperture ratio from being lowered by the sensing line 160, it is preferable that the sensing line 160 formed parallel to the data line 104 overlap

with the data line 104. Preferably, the sensing line 160 formed parallel to the gate line 102 overlaps with the gate line 102.

[0057] The common electrode contact hole 165 electrically connects the sensing line 160 with the common electrode block 180. That is, the sensing line 160 may be formed at the same layer as the pixel electrode 150. Thus, the sensing line 160 is electrically connected with the common electrode block 180 through the common electrode contact hole 165.

[0058] In this case, the common electrode contact hole 165 may be formed in a non-transmission area so as to prevent the aperture ratio from being lowered. The non-transmission area corresponds to the remaining area of pixel except an area for transmitting light, for example, the gate line 102 and the data line 104.

[0059] In FIG. 3, the common electrode contact hole 165 is positioned adjacent to the data line 104 and the source electrode 135, but not necessarily.

[0060] At least one slit 190 may be formed inside the pixel electrode 150 or common electrode block 180.

[0061] If the slit 190 is provided inside the pixel electrode 150 or common electrode block 180, a fringe field is formed between the pixel electrode 150 and the common electrode block 180 through the slit 190, whereby the liquid crystal is driven by the fringe field. That is, it is possible to realize a fringe field switching mode LCD device.

[0062] If the slit 190 is provided inside the common electrode block 180, the plurality of common electrode blocks 180 are formed on the pixel electrode 150 under the condition that a second passivation layer 170 is interposed between the common electrode block 180 and the pixel electrode 150 (See FIG. 4).

[0063] In contrast, if the slit 190 is provided inside the pixel electrode 150, the pixel electrode 150 is formed on the common electrode block 180 under the condition a second passivation layer 170 is interposed between the common electrode block 180 and the pixel electrode 150 (See FIG. 5).

[0064] The lower substrate 100 and the upper substrate 200 confronting each other are bonded to each other, and a liquid crystal layer is formed between the lower substrate 100 and the upper substrate 200.

[0065] The multiplexer (MUX) 300 is combined between the sensing line 160 and the sensing circuit 400 so as to decrease the number of sensing lines 160 input to the sensing circuit 400.

[0066] FIG. 2A illustrates an example showing the multiplexer 300 with 4:1 ratio, but not necessarily. For example, the multiplexer 300 with 8:1 ratio or 16:1 ratio may be used.

[0067] If using the multiplexer 300, it is possible to decrease the number of sensing lines 160 input to the sensing circuit 400, whereby a bezel width is decreased, or the aperture ratio is increased in the periphery.

[0068] The multiplexer 300 may be formed on the lower substrate 100 with the sensing line 160, may be provided inside a drive IC, or may be provided as an additional multiplexer chip.

[0069] The sensing circuit 400 may be directly connected with the sensing line 160 or connected with the multiplexer 300, whereby a touch sensing signal is generated when the user's touch is sensed.

[0070] Hereinafter, LCD devices according to the embodiments of the present invention will be described with reference to FIGS. 4 to 7 showing the cross sectional structures.

[0071] FIG. 4 is a cross sectional view showing one embodiment along B-B' of FIG. 3. As shown in FIG. 4, the LCD device according to the present invention includes a lower substrate 100, a gate electrode 110, a gate insulating film 120, a semiconductor layer 130, an etch stopper 133, a source electrode 135, a drain electrode 137, a first passivation layer 140, a pixel electrode 150, a sensing line 160, a second passivation layer 170, and a common electrode block 180. The LCD device according to the present invention is formed in a common electrode top structure where the common electrode block 180 is formed above the pixel electrode 150.

[0072] The lower substrate 100 may be formed of glass or transparent plastic.

[0073] The gate electrode 110 is formed on the lower substrate 100, wherein the gate electrode 110 is diverged from the gate line 102. The gate electrode 110 is formed of a conductive material.

[0074] The gate insulating film 120 is formed on the gate electrode 110, wherein the gate insulating layer 120 is formed of silicon oxide (SiO_x) or silicon nitride (SiN_x).

[0075] The semiconductor layer 130 is formed on a predetermined portion of the gate insulating film 120, wherein the semiconductor layer 130 is positioned above the gate electrode 110. Also, a channel is formed between the source electrode 135 and the drain electrode 137, wherein a current flows through the channel when a gate voltage is applied to the gate electrode 110. The semiconductor layer 130 may be formed of oxide or amorphous semiconductor.

[0076] The etch stopper 133 is formed on the semiconductor layer 130, to thereby protect the semiconductor layer 130. The etch stopper 133 may be formed of silicon oxide (SiO_x) or silicon nitride (SiN_x). If needed, it is possible to omit the etch stopper 133.

[0077] The source electrode 135 extends from the data line 104. The source electrode 135 is formed of a conductor with low resistance so as to minimize an operation delay of thin film transistor caused by a panel load.

[0078] The drain electrode 137 is formed on the semiconductor layer 130, wherein the drain electrode 137 is provided at a predetermined interval from the source electrode 135. The drain electrode 137 is formed of a conductor, and more particularly, a transparent conductor such as Indium-Tin-Oxide (ITO).

[0079] The first passivation layer 140 is formed on the source electrode 135 and the drain electrode 137, wherein the first passivation layer 140 is formed of silicon oxide (SiO_x) or silicon nitride (SiN_x).

[0080] The pixel electrode 150 is formed on the first passivation layer 140, wherein the pixel electrode 150 is formed of a transparent conductor such as Indium-Tin-Oxide (ITO). The pixel electrode 150 is electrically connected with the drain electrode 137 through a pixel electrode contact hole 155 formed in the first passivation layer 140.

[0081] The sensing line 160 is formed at the same layer as the pixel electrode 150, wherein the sensing line 160 is positioned at a predetermined interval from the pixel electrode 150. The sensing line 160 may be formed of any one selected among molybdenum (Mo), aluminum (Al) and copper (Cu), or their alloys.

[0082] The second passivation layer 170 is formed on the pixel electrode 150 and the sensing line 160, wherein the second passivation layer 170 is formed of silicon oxide (SiO_x) or silicon nitride (SiN_x).

[0083] The common electrode block 180 is formed on the second passivation layer 170, wherein the common electrode block 180 may be formed of a transparent conductor such as Indium-Tin-Oxide (ITO). The common electrode block 180 is electrically connected with the sensing line 160 through a common electrode contact hole 165 formed in the second passivation layer 170.

[0084] The common electrode block 180 is provided with a slit 190. Through the slit 190, a fringe field is formed between the pixel electrode 150 and the common electrode block 180 whereby liquid crystal is driven by the fringe field, thereby realizing a fringe field switching mode LCD device.

[0085] FIG. 5 is a cross sectional view showing another embodiment along B-B' of FIG. 3. As shown in FIG. 5, the LCD device according to the present invention includes a lower substrate 100, a gate electrode 110, a gate insulating film 120, a semiconductor layer 130, an etch stopper 133, a source electrode 135, a drain electrode 137, a first passivation layer 140, a pixel electrode 150, a sensing line 160, a second passivation layer 170, and a common electrode block 180. The LCD device according to the present invention is formed in a pixel electrode top structure where the pixel electrode 150 is formed above the common electrode block 180. Except that the pixel electrode top structure, the LCD device of FIG. 5 is identical in structure to the LCD device of FIG. 4, whereby a detailed explanation for the same parts will be omitted.

[0086] According to the embodiment of FIG. 5, after forming the first passivation layer 140, the common electrode block 180 is formed thereon. In this case, the plurality of common electrode blocks 180 may be formed at fixed intervals, to thereby prevent the common electrode block 180 from being electrically short-circuited to the pixel electrode 150 at a position of a pixel electrode contact hole 155.

[0087] After the second passivation layer 170 is formed on the common electrode block 180, the pixel electrode contact hole 135 and common electrode contact hole 165 are formed. The sensing line 160 is electrically connected with the common electrode block 180 through the common electrode contact hole 165, and the pixel electrode 150 is electrically connected with the drain electrode 137 through the pixel electrode contact hole 155.

[0088] In this case, the pixel electrode 150 is provided with a slit 190. Through the slit 190, a fringe field is formed between the pixel electrode 150 and the common electrode block 180, whereby liquid crystal is driven by the fringe field, thereby realizing a fringe field switching mode LCD device.

LCD Device Manufactured by the Use of Halftone Mask

[0089] Hereinafter, other embodiments for a structure of forming pixel electrode 150 and sensing line 160 according to the present invention will be described with reference to FIGS. 6 and 7.

[0090] FIG. 6 is a cross sectional view showing another embodiment along B-B' of FIG. 3. As shown in FIG. 6, the LCD device according to the present invention includes a lower substrate 100, a gate electrode 110, a gate insulating film 120, a semiconductor layer 130, an etch stopper 133, a

source electrode 135, a drain electrode 137, a first passivation layer 140, a pixel electrode 150, a sensing line 160, a second passivation layer 170, and a common electrode block 180. The LCD device according to the present invention is formed in a common electrode top structure where the common electrode block 180 is formed above the pixel electrode 150. Except that the pixel electrode 150 and the sensing line 160 are formed in a vertical structure, the LCD device of FIG. 6 is identical in structure to the LCD device of FIG. 4, whereby a detailed explanation for the same parts will be omitted.

[0091] According to the embodiment of FIG. 6, the pixel electrode 150 is formed under the sensing line 160. In this case, the sensing line 160 may be formed on the pixel electrode 150. However, the pixel electrode 150 overlapped with the sensing line 160 is electrically insulated from the pixel electrode 150 electrically connected with the drain electrode 137.

[0092] This structure may be obtained through steps of forming the pixel electrode 150 by a photolithography process, and then forming the sensing line 160 by another photolithography process. Instead, this structure may be obtained with efficiency by a photolithography process using a halftone mask.

[0093] That is, if the pixel electrode 150 and the sensing line 160 are simultaneously formed by the photolithography process using the halftone mask, it is possible to form the pixel electrode 150 and the sensing line 160 by using one mask instead of two masks, thereby simplifying the process.

[0094] According to an exposure process is carried out one time instead of two times, a tack time is decreased, and a cost for the exposure process is also decreased.

[0095] FIG. 7 is a cross sectional view showing another embodiment along B-B' of FIG. 3. As shown in FIG. 7, the LCD device according to the present invention includes a lower substrate 100, a gate electrode 110, a gate insulating film 120, a semiconductor layer 130, an etch stopper 133, a source electrode 135, a drain electrode 137, a first passivation layer 140, a pixel electrode 150, a sensing line 160, a second passivation layer 170, and a common electrode block 180. The LCD device according to the present invention is formed in a pixel electrode top structure where the pixel electrode 150 is formed above the common electrode block 180. Except that the pixel electrode 150 and the sensing line 160 are formed in a vertical structure, the LCD device of FIG. 7 is identical in structure to the LCD device of FIG. 5, whereby a detailed explanation for the same parts will be omitted.

[0096] According to the embodiment of FIG. 7, the pixel electrode 150 is formed under the sensing line 160. In this case, the sensing line 160 may be formed on the pixel electrode 150. However, the pixel electrode 150 overlapped with the sensing line 160 is electrically insulated from the pixel electrode 150 electrically connected with the drain electrode 137.

[0097] This structure may be obtained through steps of forming the pixel electrode 150 by a photolithography process, and then forming the sensing line 160 by another photolithography process. Instead, this structure may be obtained with efficiency by a photolithography process using a halftone mask.

[0098] That is, if the pixel electrode 150 and the sensing line 160 are simultaneously formed by the photolithography process using the halftone mask, it is possible to form the

pixel electrode 130 and the sensing line 160 by using one mask instead of two masks, thereby simplifying the process.

[0099] According to an exposure process is carried out one time instead of two times, a tack time is decreased, and a cost for the exposure process is also decreased.

LCD Device with Blocking Layer

[0100] A process of manufacturing a liquid crystal panel is referred to as a cell process. The cell process may be largely divided into an alignment process of aligning liquid crystal in a predetermined direction between a lower substrate 100 with thin film transistors arranged thereon and an upper substrate 200 with color filters; a cell gap forming process of maintaining a predetermined gap by bonding the lower substrate 100 and the upper substrate 200 to each other; a cell cutting process, and a liquid crystal injecting process.

[0101] After forming a seal pattern 250 in the cell process, liquid crystal injection is carried out by vacuum and capillary phenomenon. This liquid crystal injection method needs ten or more hours. For shortening the time, a liquid crystal dispensing and vacuum-bonding apparatus may be used so as to simultaneously carry out processes of forming a liquid crystal layer and bonding the two substrates to each other.

[0102] Through the use of liquid crystal dispensing and vacuum-bonding apparatus, an array substrate with the seal pattern 250 of UV-curing sealant and a color filter substrate are positioned to confront each other, and then an appropriate amount of liquid crystal is dispensed onto any one of the array substrate and the color filter substrate under the vacuum atmosphere before bonding the two substrates to each other. Thereafter, the two substrates are aligned and then vacuum-bonded to each other. Simultaneously, the seal pattern 250 is irradiated with ultraviolet rays (UV), and is then cured, to thereby obtain a mother substrate of liquid crystal panels. The obtained mother substrate of liquid crystal panels is cut into unit liquid crystal panels, to thereby manufacture the unit liquid crystal panel in a short time.

[0103] As described above, since an opening for injection of liquid crystal is unnecessary for the liquid crystal panel manufactured by the use of liquid crystal dispensing and vacuum-bonding apparatus, the seal pattern 250 is continuously formed without opening.

[0104] However, in order to form the seal pattern 250, the seal pattern 250 of UV-curing sealant has to be irradiated with the ultraviolet rays (UV) so as to cure the UV-curing sealant. In this case, the semiconductor layer 130 of the transistor may be deteriorated by the ultraviolet rays.

[0105] In order to prevent the semiconductor layer 130 from being deteriorated, there is proposed an LCD device according to another embodiment of the present invention which includes a blocking layer 160a for blocking the ultraviolet rays, formed on the transistor. This proposed LCD device according to another embodiment of the present invention will be described in detail with reference to FIGS. 8 to 10.

[0106] FIG. 8 illustrates an LCD device according to another embodiment of the present invention. As shown in FIG. 8, the LCD device according to another embodiment of the present invention includes a lower substrate 100, an upper substrate 200, an active area (A/A), a dummy area (N/A), a common electrode block 180, a seal pattern 250, and a sensing circuit 400.

[0107] On the lower substrate 100, there are gate and data lines 102 and 104, a plurality of transistors, a plurality of pixel electrodes 150, the plurality of common electrode

blocks **180**, the active area (A/A), and the dummy area (N/A). In this case, a plurality of pixels may be defined by the gate and data lines **102** and **104** crossing each other. Also, the plurality of transistors may be respectively formed in the pixels, and the pixel electrodes **150** may be respectively formed in the pixels. The common electrode block **180** and the pixel electrode **150** are formed at different layers, wherein the common electrode block **180**, together with the pixel electrode **150**, forms an electric field. Also, the plurality of common electrode blocks **180** are patterned to sense the user's touch. In the active area (A/A), there are a plurality of sensing lines **160** which are electrically connected with the common electrode blocks **180**. The dummy area (N/A) is formed along the edge of the active area (A/A).

[0108] On the upper substrate **200**, there is a black matrix **230** for preventing a light leakage. If needed, a color filter layer may be additionally formed on the upper substrate **200**.

[0109] The sensing circuit **400** may be directly connected with the sensing line **160** or a multiplexer (not shown) so as to generate a touch sensing signal when a user's touch is sensed.

[0110] The seal pattern **250** is formed along the dummy area (N/A) in the edge of the lower and upper substrates **100** and **200**, wherein the seal pattern **250** prevents the outflow of liquid crystal filled between the lower and upper substrates **100** and **200**.

[0111] FIG. 9 is a cross sectional view showing one embodiment along C-C' of FIG. 8. As shown in FIG. 9, the LCD device according to one embodiment of the present invention includes a lower substrate **100**, a gate electrode **110**, a gate insulating film **120**, a semiconductor layer **130**, an etch stopper **133**, a source electrode **135**, a drain electrode **137**, a first passivation layer **140**, a pixel electrode **150**, a sensing line **160b**, a blocking layer **160a**, a second passivation layer **170**, a common electrode block **180**, an upper substrate **200**, a black matrix **230**, and a seal pattern **250**. The LCD device of FIG. 9 is formed in a common electrode top structure where the common electrode block **180** is formed above the pixel electrode **150**.

[0112] The lower substrate **100** may be formed of glass or transparent plastic.

[0113] The gate electrode **110** is formed on the lower substrate **100**, wherein the gate electrode **110** is diverged from the gate line **102**. The gate electrode **110** is formed of a conductive material.

[0114] The gate insulating film **120** is formed on the gate electrode **110**, wherein the gate insulating layer **120** is formed of silicon oxide (SiOx) or silicon nitride (SiNx).

[0115] The semiconductor layer **130** is formed on a predetermined portion of the gate insulating film **120**, wherein the semiconductor layer **130** is positioned above the gate electrode **110**. Also, a channel is formed between the source electrode **135** and the drain electrode **137**, wherein a current flows through the channel when a gate voltage is applied to the gate electrode **110**. The semiconductor layer **130** may be formed of oxide or amorphous semiconductor.

[0116] The etch stopper **133** is formed on the semiconductor layer **130**, to thereby protect the semiconductor layer **130**. The etch stopper **133** may be formed of silicon oxide (SiOx) or silicon nitride (SiNx). If needed, it is possible to omit the etch stopper **133**.

[0117] The source electrode **135** extends from the data line **104**. The source electrode **135** is formed of a conductor with

low resistance so as to minimize an operation delay of thin film transistor caused by a panel load.

[0118] The drain electrode **137** is formed on the semiconductor layer **130**, wherein the drain electrode **137** is provided at a predetermined interval from the source electrode **135**. The drain electrode **137** is formed of a conductor, and more particularly, a transparent conductor such as Indium-Tin-Oxide (ITO).

[0119] The first passivation layer **140** is formed on the source electrode **135** and the drain electrode **137**, wherein the first passivation layer **140** is formed of silicon oxide (SiOx) or silicon nitride (SiNx).

[0120] A third passivation layer **145** is formed in the active area (A/A) on the first passivation layer **140**, wherein the third passivation layer **145** is formed of silicon oxide (SiOx) or silicon nitride (SiNx). If needed, it is possible to omit the third passivation layer **145**.

[0121] The pixel electrode **150** is formed on the first passivation layer **140** or the third passivation layer **145**, wherein the pixel electrode **150** is formed of a transparent conductor such as Indium-Tin-Oxide (ITO). The pixel electrode **150** is electrically connected with the drain electrode **137** through a pixel electrode contact hole **155**.

[0122] The sensing line **160b** is formed at the same layer as the pixel electrode **150**, wherein the sensing line **160** is positioned at a predetermined interval from the pixel electrode **150**. The sensing line **160** may be formed of any one selected among molybdenum (Mo), aluminum (Al) and copper (Cu), or their alloys.

[0123] In this case, the sensing line **160b** is formed in a size corresponding to a size of the semiconductor layer **130** of the transistor formed below the sensing line **160b**. That is, the sensing line **160b** transfers a user's touch signal to the sensing circuit **400**, and furthermore prevents deterioration of the semiconductor layer **130** by preventing ultraviolet rays from being incident on the semiconductor layer **130**.

[0124] The blocking layer **160a** is formed above the semiconductor layer **130** of the transistor in the dummy area (N/A), whereby it is possible to prevent deterioration of the semiconductor layer **130** by preventing ultraviolet rays from being incident on the semiconductor layer **130**.

[0125] The blocking layer **160a** and the sensing line **160b** may be formed separately, that is, the blocking layer **160a** may be formed by an additional process. The blocking layer **160a** may be formed on the other layer instead of the first passivation layer **140**. However, the blocking layer **160a** may be formed of the same material as the sensing line **160b** during a process for forming the sensing line **160b**. That is, a process for forming the sensing line **160b** and a process for forming the blocking layer **160a** may be carried out at the same time, whereby it is possible to decrease process time and cost in comparison with those in a case of separately forming the sensing line **160b** and the blocking layer **160a**.

[0126] The transistor formed in the dummy area (N/A) includes, a transistor on a Gate-In-Panel (GIP) structure where a gate driving circuit is provided inside a panel, a transistor on an ESD structure for an electrostatic discharge, a transistor of an auto probe for a lighting test, and a transistor for an engineer test.

[0127] The second passivation layer **170** is formed on the pixel electrode **150** and the sensing line **160**, wherein the second passivation layer **170** is formed of silicon oxide (SiOx) or silicon nitride (SiNx).

[0128] The common electrode block **180** is formed on the second passivation layer **170**, wherein the common electrode block **180** may be formed of a transparent conductor such as Indium-Tin-Oxide (ITO). The common electrode block **180** is electrically connected with the sensing line **160** through a common electrode contact hole **165** formed in the second passivation layer **170**.

[0129] The common electrode block **180** is provided with a slit **190**. Through the slit **190**, a fringe field is formed between the pixel electrode **150** and the common electrode block **180**, whereby liquid crystal is driven by the fringe field, thereby realizing a fringe field switching mode LCD device.

[0130] The blade matrix **230** is formed on the upper substrate **200**, wherein the black matrix **230** is positioned in a region for preventing a light leakage except a pixel region of the lower substrate **100**.

[0131] The seal pattern **250** is formed in the edge of the lower and upper substrates **100** and **200**, to thereby prevent a leakage of liquid crystal layer.

[0132] FIG. 10 is a cross sectional view showing another embodiment along C-C' of FIG. 8. As shown in FIG. 10, the LCD device according to another embodiment of the present invention includes a lower substrate **100**, a gate electrode **110**, a gate insulating film **120**, a semiconductor layer **130**, an etch stopper **133**, a source electrode **135**, a drain electrode **137**, a first passivation layer **140**, a pixel electrode **150**, a sensing line **160b**, a blocking layer **160a**, a second passivation layer **170**, a common electrode block **180**, an upper substrate **200**, a black matrix **230**, and a seal pattern **250**. The LCD device of FIG. 10 is formed in a pixel electrode top structure where the pixel electrode **150** is formed above the common electrode block **180**. Herein, a detailed explanation for the parts repeated in FIG. 9 will be omitted.

[0133] After forming the common electrode block **180** on the first passivation layer **140**, the second passivation layer **170** is formed on the common electrode block **180**. FIG. 10 illustrates that the second passivation layer **170** is positioned inside the liquid crystal panel with reference to the seal pattern **250**, but not necessarily. The second passivation layer **170** may be formed at the lower side of the seal pattern **250**.

[0134] In the second passivation layer **170**, there are a common electrode contact hole **165** for electrically connecting the sensing line **160b** and the common electrode block **180** with each other, and a pixel electrode contact hole **155** for electrically connecting the drain electrode **137** and the pixel electrode **150** with each other.

[0135] The sensing line **160b** is formed on the second passivation layer **170**, wherein the sensing line **160b** is electrically connected with the common electrode block **180**. Also, the pixel electrode **150** being electrically connected with the drain electrode **137** is formed on the second passivation layer **170**. In this case, the pixel electrode **150** is provided with a slit **190**. Through the slit **190**, a fringe field is formed between the pixel electrode **150** and the common electrode block **180**, whereby liquid crystal is driven by the fringe field, thereby realizing a fringe field switching mode LCD device.

Method for Manufacturing LCD Device

[0136] FIGS. 11A to 11C are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to one embodiment of the present invention.

[0137] As shown in FIG. 11A, the gate electrode **110**, the gate insulating film **120**, the semiconductor layer **130**, the etch stopper **133**, the source electrode **135**, the drain electrode **137**, and the first passivation layer **140** are sequentially formed on the lower substrate **100**. Although not shown, the gate line **102** and the data line **104** are formed on the lower substrate **100**.

[0138] As shown in FIG. 11B, after the pixel electrode contact hole **155** is formed on the first passivation layer **140**, the pixel electrode **150** is formed while being electrically connected with the drain electrode **137**. Also, the sensing line **160** is formed on the predetermined portion of the first passivation layer **140**.

[0139] The sensing line **160** may be formed in a direction parallel to the gate line **102** or the data line **104**. According to the present invention, even though the sensing line **160** is formed in a direction parallel to the gate line **102** or the data line **104**, it is possible to sense the user's touch position on the X-Y coordinates plane.

[0140] In order to prevent the aperture, ratio from being lowered by the sensing line **160**, it is preferable that the sensing line **160** formed parallel to the data line **104** overlap with the data line **104**. Preferably, the sensing line **160** formed parallel to the gate line **102** overlaps with the gate line **102**.

[0141] As shown in FIG. 11C, after the second passivation layer **170** is formed on the pixel electrode **150** and the sensing line **160**, the common electrode contact hole **165** is formed to electrically connect the sensing line **160** and the common electrode block **180** to each other.

[0142] By adjusting the position of the common electrode contact hole **165**, when the sensing line **160** is electrically connected with one of the common electrode blocks **180**, the sensing line **160** is insulated from the remaining common electrode blocks **180**.

[0143] The common electrode block **180** is formed on the second passivation layer **170**, to thereby electrically connect the sensing line **160** and the common electrode block **180** to each other.

[0144] In order to use the common electrode block **180** as the sensing electrode, the plurality of common electrode blocks **180** are patterned. The plurality of common electrode blocks **180** may be formed in a size corresponding to a size of one or more pixels. Herein, the size of common electrode blocks **180** deeply affects touch resolution of the LCD device. That is, the touch resolution of the LCD device is highly affected by the number of pixels to be corresponding to the size of common electrode blocks **180**.

Method for Manufacturing LCD Device by the Use of Halftone Mask

[0145] FIGS. 12A to 12D are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to another embodiment of the present invention. Herein, only non-repeated parts, which are not described in FIGS. 11A to 11C, will be chiefly described in detail.

[0146] First, as shown in FIG. 12A, the gate electrode 110, the gate insulating film 120, the semiconductor layer 130, the etch stopper 133, the source electrode 135, the drain electrode 137, and the first passivation layer 140 are sequentially formed on the lower substrate 100. Then, the pixel electrode contact hole 155 is formed on the first passivation layer 140.

[0147] As shown in FIG. 12B, a pixel electrode layer 150a and a sensing line layer 140a are sequentially formed on the first passivation layer 140.

[0148] Then, a photoresist is deposited on the pixel electrode layer 150a and the sensing line layer 140a, and the deposited photoresist is irradiated with light through the use of halftone mask 700. In this case, the halftone mask includes a non-transmission area 710 through which light does not penetrate, a semi-transmission area 720 through which some of light penetrate, and a transmission area 730a, 730b and 730c through which light penetrates totally.

[0149] Thereafter, the photoresist is developed to thereby form a photoresist pattern. The photoresist pattern is provided in such a manner that the photoresist layer corresponding to the non-transmission area 710 of the halftone mask remains as it is, the photoresist layer corresponding to the semi-transmission area 720 of the halftone mask remains partially, and the photoresist layer corresponding to the transmission area 730a, 730b and 730c is completely removed.

[0150] As shown in FIG. 12C, under the condition that the photoresist pattern is used as a mask, the pixel electrode layer 150a and the sensing line layer 140a are etched. After ashing the photoresist pattern, the etching process is carried out again, and then the photoresist pattern is removed.

[0151] If the pixel electrode 150 and the sensing line 160 are formed in the aforementioned method, it is possible to carry out the light-irradiation process once, to thereby decrease the manufacturing time and cost.

[0152] As shown in FIG. 12D, the second passivation layer 170 is formed on the pixel electrode 150 and the sensing line 160, and then the common electrode block 180 is patterned on the second passivation layer 170.

Method for Manufacturing LCD Device with Blocking Layer

[0153] FIGS. 13A to 13D are cross sectional views showing a process for manufacturing the lower substrate for the LCD device according to another embodiment of the present invention. Herein, only non-repeated parts, which are not described in FIGS. 11A to 11C, will be chiefly described in detail.

[0154] First, as shown in FIG. 13A, the gate electrode 110, the gate insulating film 120, the semiconductor layer 130, the etch stopper 133, the source electrode 135, the drain electrode 137, the first passivation layer 140, and the third passivation layer 145 are sequentially formed on the lower substrate 100. Then, the pixel electrode contact hole 155 is formed in the first passivation layer 140 and the third passivation layer 145.

[0155] As shown in FIG. 13B, the pixel electrode 150 is patterned on the third passivation layer 145, wherein the pixel electrode 150 is electrically connected with the drain electrode 137. After that, the sensing line 160b is formed on the third passivation layer 145. Also, the blocking layer 160a is formed on the first passivation layer 140.

[0156] Each of the sensing line 160b and the blocking layer 160a is provided in the size corresponding to that of

the semiconductor layer 130 formed therebelow, to thereby prevent the ultraviolet rays irradiated from the upper side from being incident on the semiconductor layer 130.

[0157] As shown in FIG. 13C, the second passivation layer 170 is formed on the pixel electrode 150, the sensing line 160b, and the blocking layer 160a, and the common electrode contact hole 165 is formed to electrically connect the sensing line 160b and the common electrode block 180 with each other.

[0158] Then, as shown in FIG. 13D, the lower substrate 100 and the upper substrate 200 confronting each other are bonded to each other, and the liquid crystal layer is formed by injecting liquid crystal into the space between the lower substrate 100 and the upper substrate 200, and is then cured by irradiation of ultraviolet rays, to thereby form the seal pattern 250.

[0159] According as the blocking layer 160a and the sensing line 160b are formed on the semiconductor layer 130, it is possible to prevent the semiconductor layer 130 from being deteriorated by the ultraviolet rays.

Method for Manufacturing LCD Device with High-Resistance Conductive Layer on Rear Surface of Upper Substrate

[0160] FIG. 14 is a cross sectional view showing another embodiment along C-C' of FIG. 8. As shown in FIG. 14, the LCD device according to another embodiment of the present invention includes the lower substrate 100, the gate electrode 110, the gate insulating film 120, the semiconductor layer 130, the etch stopper 133, the source electrode 135, the drain electrode 137, the first passivation layer 140, the pixel electrode 150, the sensing line 160b, the blocking layer 160a, the second passivation layer 170, the common electrode block 180, the upper substrate 200, the black matrix 230, the seal pattern 250, and a high-resistance conductive layer 270. The LCD device according to the present invention is formed in a common electrode top structure where the common electrode block 180 is formed above the pixel electrode 150. Herein, a detailed explanation for the same parts as those of FIG. 9 will be omitted.

[0161] The high-resistance conductive layer 270 is formed on the rear surface of the upper substrate 200. The high-resistance conductive layer 270 is formed a transparent conductive material with optical transparency for penetrating light emitted from the liquid crystal panel, and electrical conductivity for grounding (GND) electric charges formed in the lower substrate 100 by static electricity toward a ground pad (not shown). In order to enhance the function of sensing the user's touch position, the high-resistance conductive layer 270 may have high resistance (for example, 50 MΩ/sqr~5 GΩ/sqr).

[0162] The high-resistance conductive layer 270 enables to discharge the electric charges from the liquid crystal panel into the ground (GND), to thereby improve ESD shielding efficiency of the LCD device with touch screen provided therein.

[0163] That is, as mentioned above, since the high-resistance conductive layer 270 is formed of the high-resistance material with the above resistance value of 50 MΩ/sqr~5 GΩ/sqr, it is possible to prevent, a phenomenon of shielding influence of user finger, to thereby improve touch sensing efficiency of the LCD device with touch screen provided therein.

[0164] Accordingly, the LCD device according to the present invention uses the common electrode, provided for formation of the electric field to drive the liquid crystal, as

the sensing electrode. That is, there is no need for the additional touch screen of the related art on the upper surface of the liquid crystal panel. Thus, the present invention enables to decrease the total thickness of the device, to simplify the manufacturing process, and to decrease the manufacturing cost.

[0165] According to the present invention, the user's touch position is sensed on the X-Y coordinates plane through the use of sensing line formed in only one direction of the lower substrate. Thus, in comparison with the related art LCD device with the sensing lines provided in the X-axis direction and the Y-axis direction, the LCD device according to the present invention is provided with the simplified structure, to thereby decrease the manufacturing cost.

[0166] According to the present invention, it is possible to decrease the number of sensing lines input to the sensing circuit by the use of multiplexer (MUX), whereby the bezel width is decreased, or the aperture ratio is increased in the periphery.

[0167] According to the present invention, the sensing line and the pixel electrode are patterned by one mask process, thereby decreasing the manufacturing time and cost.

[0168] According to the present invention, the blocking layer for blocking ultraviolet rays is formed on the semi-

conductor layer, to thereby prevent the semiconductor layer from being deteriorated by the ultraviolet rays.

[0169] It will be apparent to those skilled in the art that various modifications and variations can be made in the present invention without departing from the spirit or scope of the inventions. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

1-18. (canceled)

19. A display device with an integrated touch screen, comprising:

- a first electrode;
- a second electrode insulated from the first electrode;
- a sensing line electrically connected with the second electrode; and
- a sensing circuit electrically connected with the sensing line, wherein an electrical signal is applied to the second electrode via the sensing line, and the sensing circuit detects a touch from the second electrode via the sensing line.

* * * * *

专利名称(译)	显示装置及其制造方法		
公开(公告)号	US20180252956A1	公开(公告)日	2018-09-06
申请号	US15/970716	申请日	2018-05-03
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	SHIN HEESUN LEE SEOK WOO YU JAE SUNG KIM JU HAN LEE SUN JUNG SONG IN HYUK		
发明人	SHIN, HEESUN LEE, SEOK WOO YU, JAE SUNG KIM, JU HAN LEE, SUN JUNG SONG, IN HYUK		
IPC分类号	G02F1/1333 G02F1/1335 G02F1/1343 G06F3/041 G02F1/1362 G06F3/047 G06F3/044 G02F1/1368		
CPC分类号	G06F3/041 G02F2001/134372 G02F1/133514 G02F2001/133302 G02F2001/136295 G02F1/133345 G06F3/047 G02F1/134309 G02F1/13439 G02F1/136286 G02F1/1368 G06F2203/04103 G06F3/044 G06F3/0412 G02F1/13338		
优先权	1020110140094 2011-12-22 KR		
其他公开文献	US10718968		
外部链接	Espacenet USPTO		

摘要(译)

本发明公开了一种LCD装置，其通过使用用于形成电场的公共电极来驱动液晶作为感测电极，并且从液晶面板的上表面移除触摸屏，实现了厚度减小，工艺简化和成本降低，LCD装置包括彼此交叉的栅极线和数据线，以在下基板上限定多个像素；多个像素中的每个像素中的像素电极；多个公共电极块在与像素电极不同的层处形成图案，其中公共电极块与像素电极一起形成电场，并感测用户的触摸；多个感测线与公共电极块电连接，其中，如果感测线与公共电极块中的一个电连接，则感测线与其余的公共电极块绝缘。

